

**SEMICONDUCTOR DEVICE WITH MODIFIED CHANNEL COMPRESSIVE
ABSTRACT**

[0029] A semiconductor device and the method for making same is disclosed. The semiconductor device has a substrate and a gate region on top of the substrate. It further has a first and second gate sidewall liners situated on a first and second sides of the gate region respectively, the first and second sidewall liners having a vertical part contacting sidewalls of the gate region and a horizontal part contacting the substrate; and a first and second recessed spacers situated on top of the first and second sidewall liners respectively, wherein a height of the first and second spacers is lower than a height of the gate sidewall liner and wherein the width of the horizontal part of the sidewall liner is shorter than the width of the spacer.